

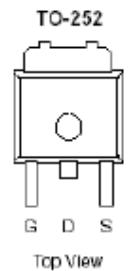
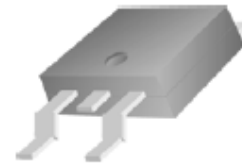
N-Channel 100-V (D-S) MOSFET

Key Features:

- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

Typical Applications:

- PoE Power Sourcing Equipment
- PoE Powered Devices
- Telecom DC/DC converters
- White LED boost converters



PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (m Ω)	I_D (A)
100	280 @ $V_{GS} = 10V$	11
	355 @ $V_{GS} = 4.5V$	10

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	11	A
Pulsed Drain Current ^b	I_{DM}	50	
Continuous Source Current (Diode Conduction)	I_S	28	A
Power Dissipation	P_D	50	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ C$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	40	$^\circ C/W$
Maximum Junction-to-Case	$R_{\theta JC}$	3	

Notes

- Surface Mounted on 1" x 1" FR4 Board, drain pad using 2 oz copper, value dependent on PC board thermal characteristics
- Pulse width limited by maximum junction temperature

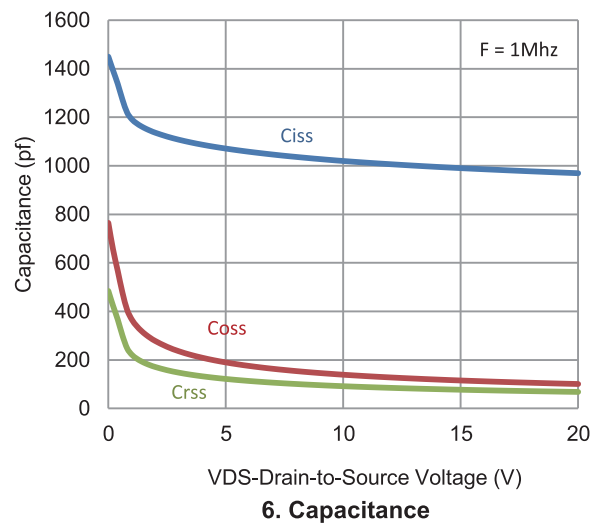
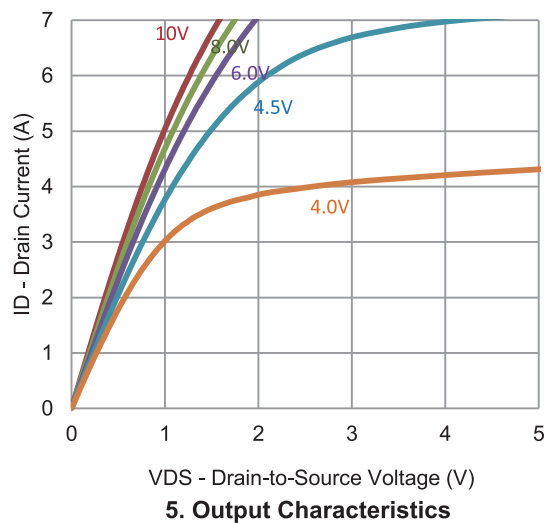
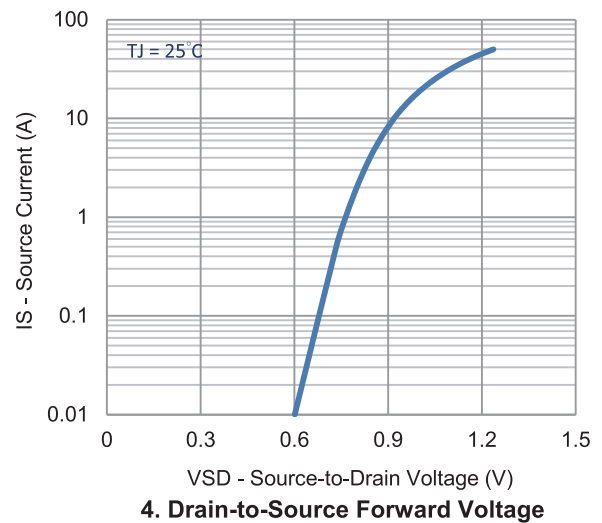
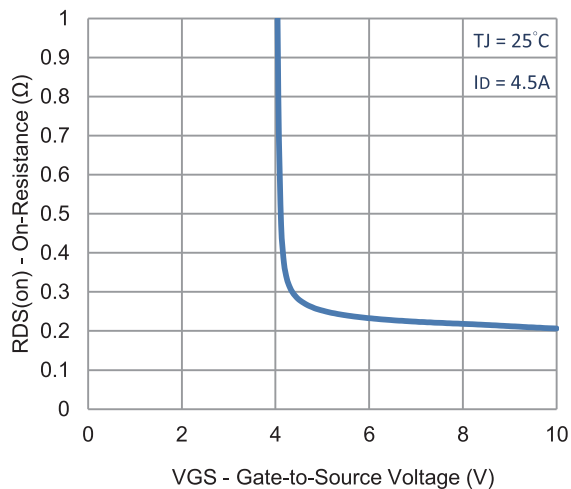
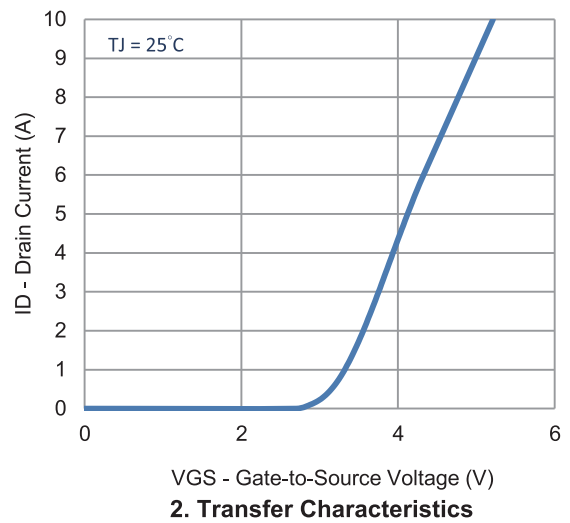
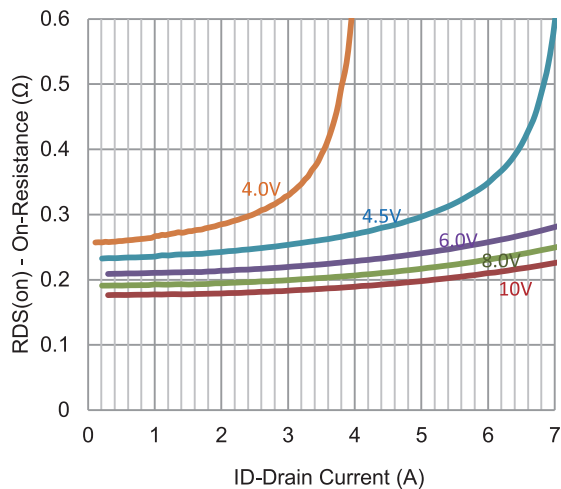
Typical Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1		3.5	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V$, $V_{GS} = 20 V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80 V$, $V_{GS} = 0 V$			1	μA
		$V_{DS} = 80 V$, $V_{GS} = 0 V$, $T_J = 55^\circ C$			25	
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 V$, $V_{GS} = 10 V$	34			A
Drain-Source On-Resistance	$r_{DS(on)}$	$V_{GS} = 10 V$, $I_D = 4.5 A$			280	m Ω
		$V_{GS} = 4.5 V$, $I_D = 4 A$			355	
Forward Transconductance	g_{fs}	$V_{DS} = 15 V$, $I_D = 4.5 A$		5		S
Diode Forward Voltage	V_{SD}	$I_S = 14 A$, $V_{GS} = 0 V$		0.95		V
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = 50 V$, $V_{GS} = 4.5 V$, $I_D = 4.5 A$		3.8		nC
Gate-Source Charge	Q_{gs}			1.3		
Gate-Drain Charge	Q_{gd}			1.7		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50 V$, $R_L = 14.3 \Omega$, $I_D = 4.5 A$, $V_{GEN} = 10 V$, $R_{GEN} = 6 \Omega$		4.8		nS
Rise Time	t_r			3.9		
Turn-Off Delay Time	$t_{d(off)}$			12.7		
Fall Time	t_f			3.2		
Input Capacitance	C_{iss}	$V_{DS} = 15 V$, $V_{GS} = 0 V$, $f = 1 MHz$		332		pF
Output Capacitance	C_{oss}			40		
Reverse Transfer Capacitance	C_{rss}			29		
Gate Resistance	R_g	$f = 1 MHz$		0.3		Ω

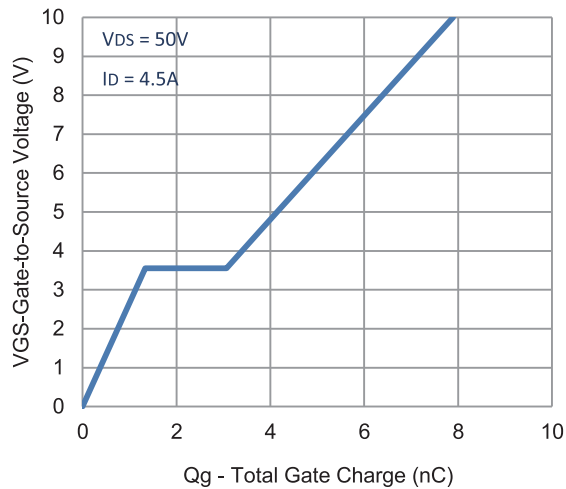
Notes

- Pulse test: $PW \leq 300 \mu s$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

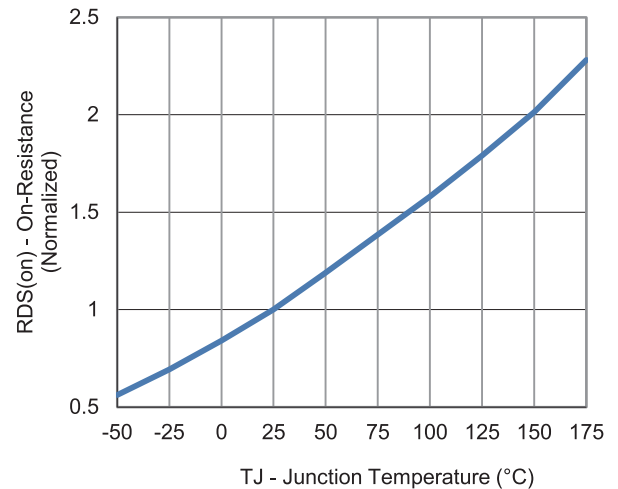
Typical Electrical Characteristics



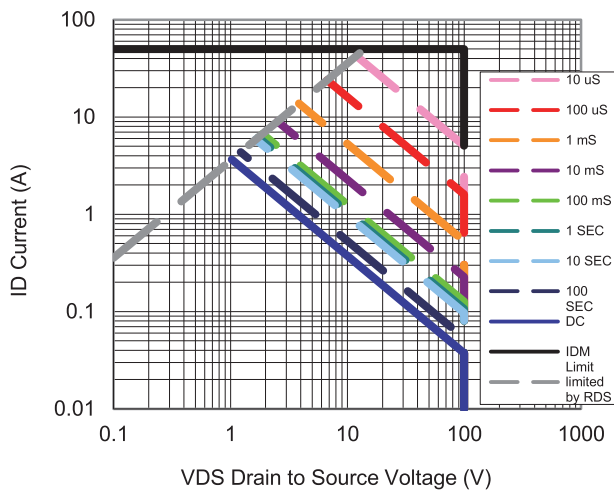
Typical Electrical Characteristics



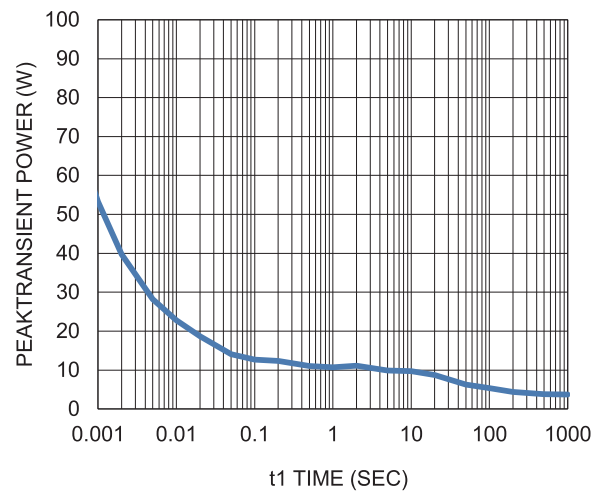
7. Gate Charge



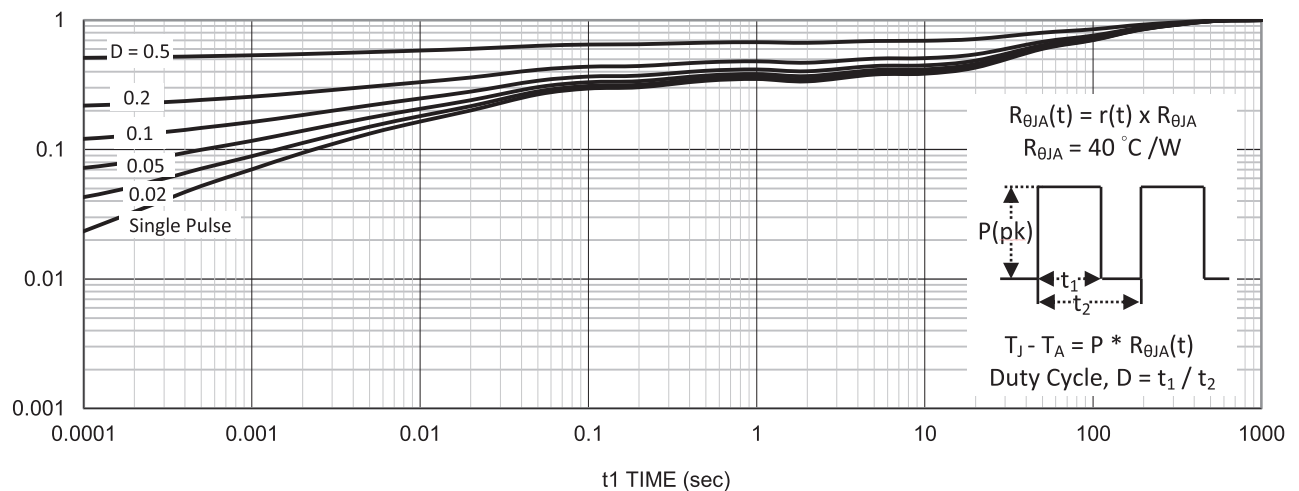
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

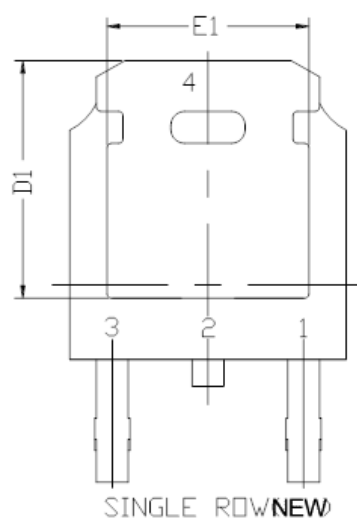
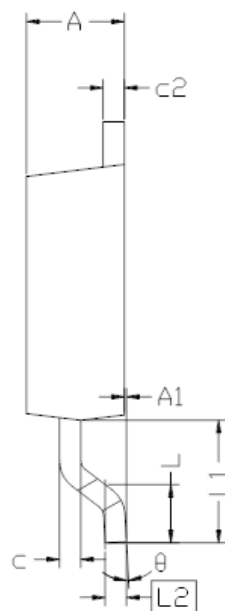
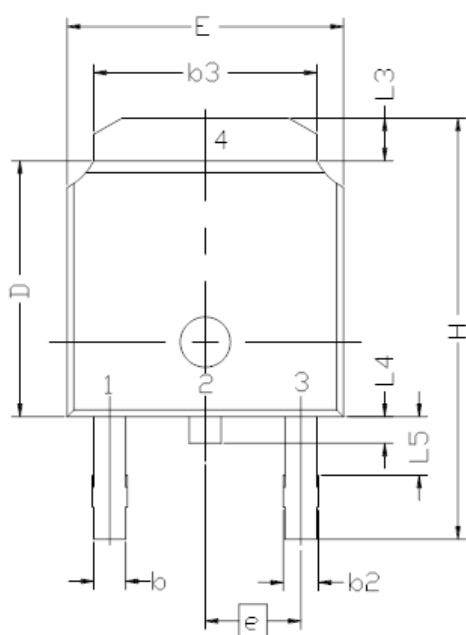


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2.743 REF		
L2	0.508 BSC		
L3	0.89	--	1.27
L4	0.64	--	1.01
L5	--	--	--
D	6.00	6.10	6.223
H	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e	2.286 BSC		
A	2.20	2.30	2.38
A1	0	--	0.127
c	0.45	0.50	0.60
c2	0.45	0.50	0.58
D1	5.30	--	--
E1	4.40	--	--
θ	0°	--	10°

Note:

1. All Dimension Are In mm.
2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.